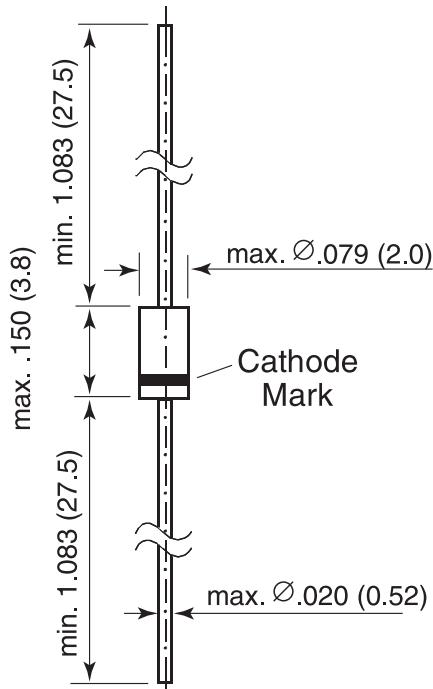


Small-Signal Diodes

DO-35 Glass



Dimensions in inches and (millimeters)

Features

- Silicon Epitaxial Planar Diodes
- For general purpose
- This diode is also available in other case styles including: the SOD-123 case with the type designation BAV19W to BAV21W, the MiniMELF case with the type designation BAV101 to BAV103, the SOT-23 case with the type designation BAS19 to BAS21, and the SOD-323 case with type designation BAV19WS to BAV21WS.

Mechanical Data

Case: DO-35 Glass Case

Weight: approx. 0.13g

Maximum Ratings and Thermal Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

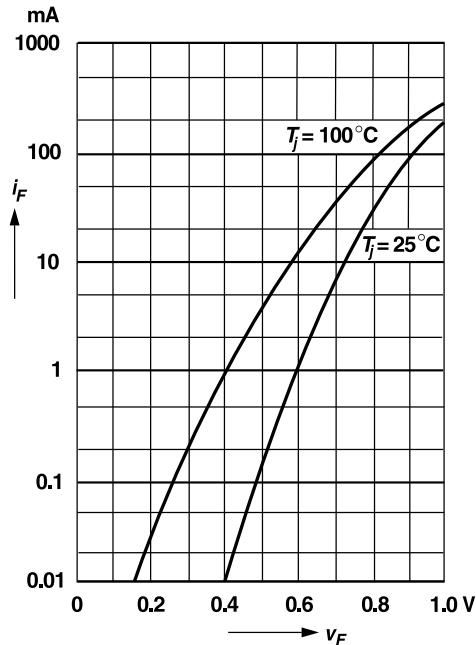
Parameter		Symbol	Value	Unit
Continuous Reverse Voltage BAV19 BAV20 BAV21		VR	100	V
			150	
			200	
Repetitive Peak Reverse Voltage BAV19 BAV20 BAV21		VR _{RM}	120	V
			200	
			250	
Forward DC Current at $T_{\text{amb}} = 25^\circ\text{C}^{(1)}$		I _F	250	mA
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{\text{amb}} = 25^\circ\text{C}^{(1)}$		I _{F(AV)}	200	mA
Repetitive Peak Forward Current at $f \geq 50\text{Hz}$, $\Theta = 180^\circ$, $T_{\text{amb}} = 25^\circ\text{C}^{(1)}$		I _{FRM}	625	mA
Surge Forward Current at $t < 1\text{s}$, $T_j = 25^\circ\text{C}$		I _{FSM}	1	A
Power Dissipation at $T_{\text{amb}} = 25^\circ\text{C}^{(1)}$		P _{tot}	500	mW
Thermal Resistance Junction to Ambient Air ⁽¹⁾		R _{θJA}	430	°C/W
Junction Temperature ⁽¹⁾		T _j	175	°C
Storage Temperature Range ⁽¹⁾		T _s	-65 to +175	°C

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F = 100mA I _F = 200mA	—	—	1.00 1.25	V
Leakage Current BAV19 BAV19 BAV20 BAV20 BAV21 BAV21	I _R	V _R = 100V	—	—	100	nA
		V _R = 100V, T _j = 100°C	—	—	15	μA
		V _R = 150V	—	—	100	nA
		V _R = 150V, T _j = 100°C	—	—	15	μA
		V _R = 200V	—	—	100	nA
		V _R = 200V, T _j = 100°C	—	—	15	μA
Dynamic Forward Resistance	r _f	I _F = 10mA	—	5	—	Ω
Capacitance	C _{tot}	V _R = 0, f = 1MHz	—	1.5	—	pF
Reverse Recovery Time	t _{rr}	I _F = 30mA, I _R = 30mA I _{rr} = 3mA, R _L = 100Ω	—	—	50	ns

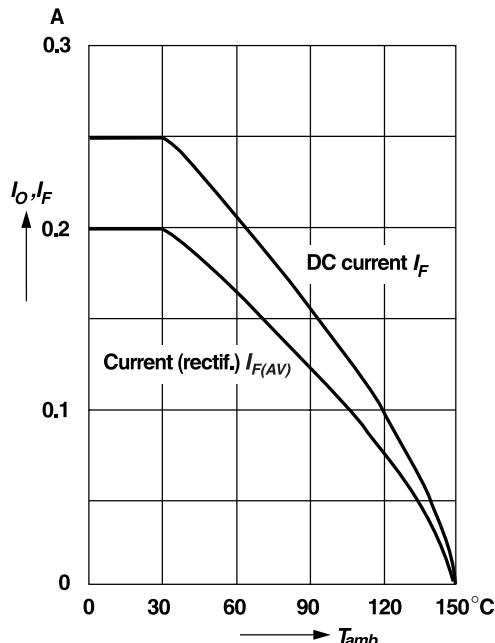
Ratings and Characteristic Curves (T_A = 25°C unless otherwise noted)

Forward characteristics



Admissible forward current versus ambient temperature

Valid provided that electrodes are kept at ambient temperature

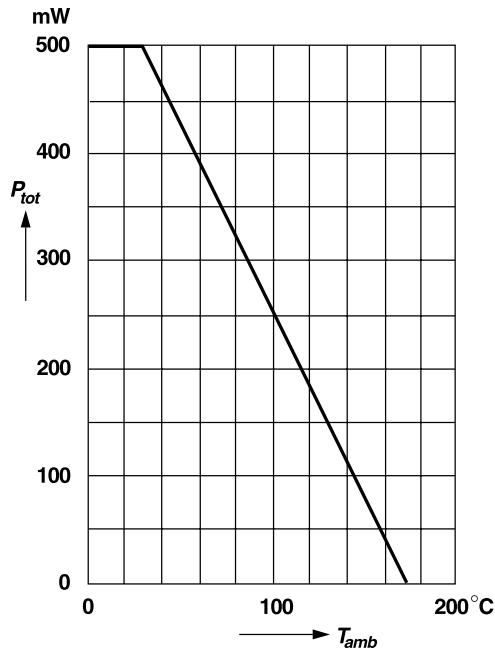


BAV19 thru BAV21

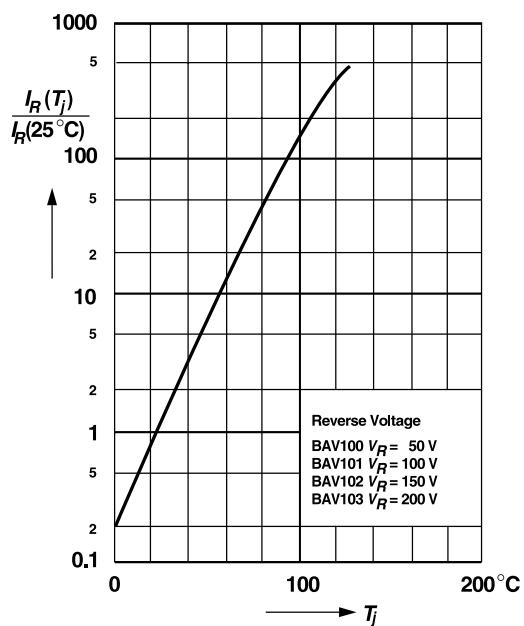
Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Admissible power dissipation versus ambient temperature

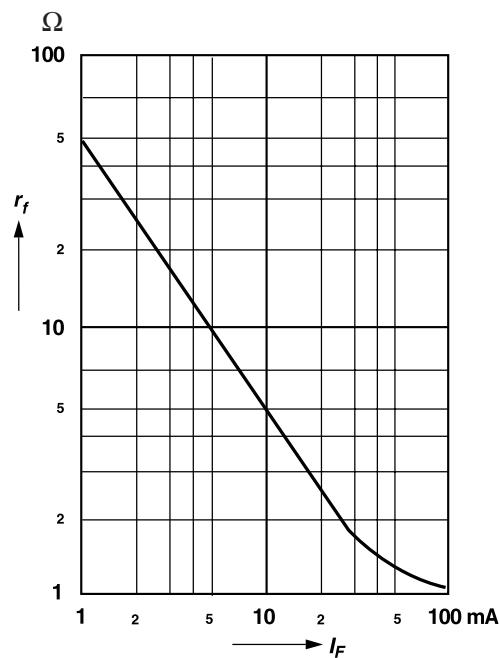
Valid provided that electrodes are kept at ambient temperature



Leakage current versus junction temperature



Dynamic forward resistance versus forward current



Capacitance versus reverse voltage

